

General Description

The MY3402 is the high cell density trenchd N-CH MOSFET, which provides excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load switch applications.

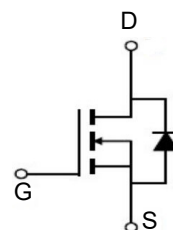
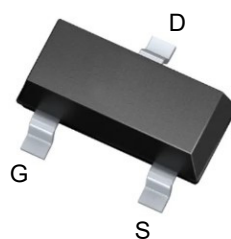


Features

V_{DSS}	30	V
I_D	5	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 45	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 65	m Ω

Application

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY3402	SOT-23	MY3402	3000

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	5	A
Pulsed Drain Current (note 1)	I_{DM}	15	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

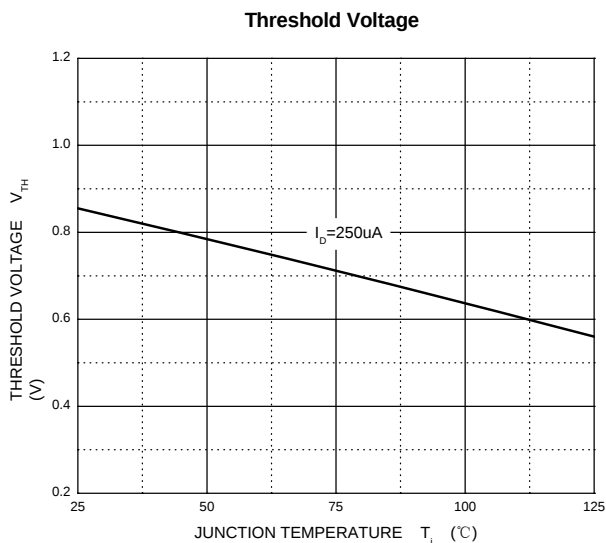
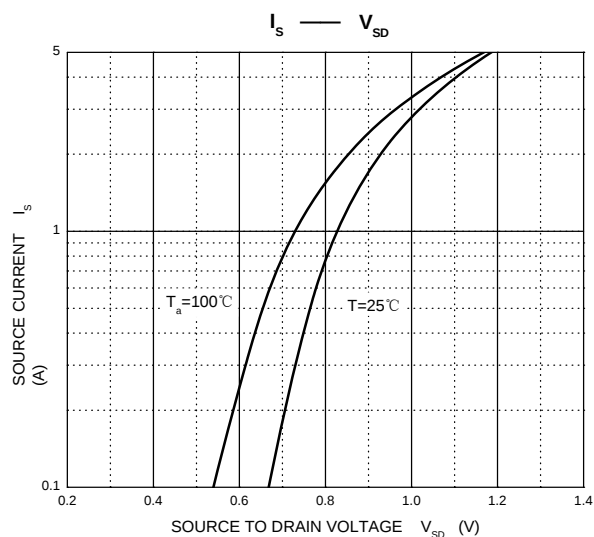
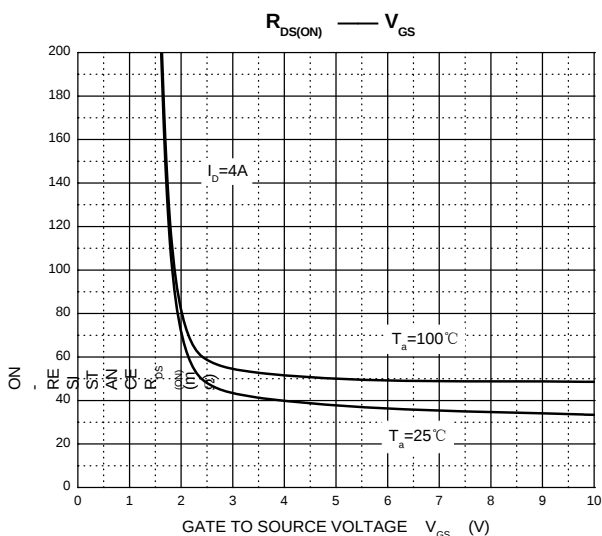
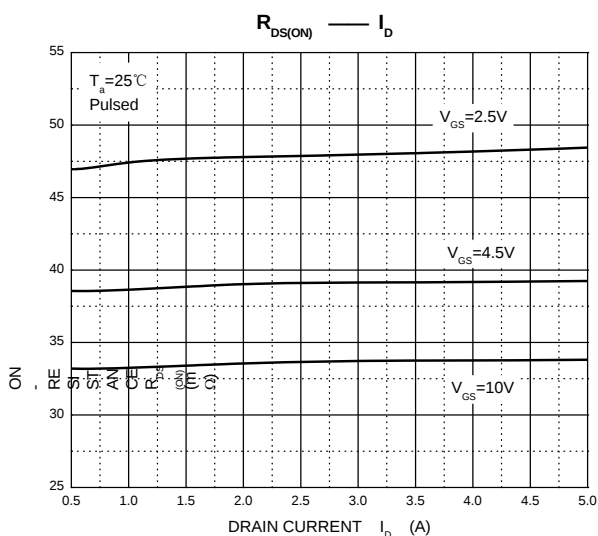
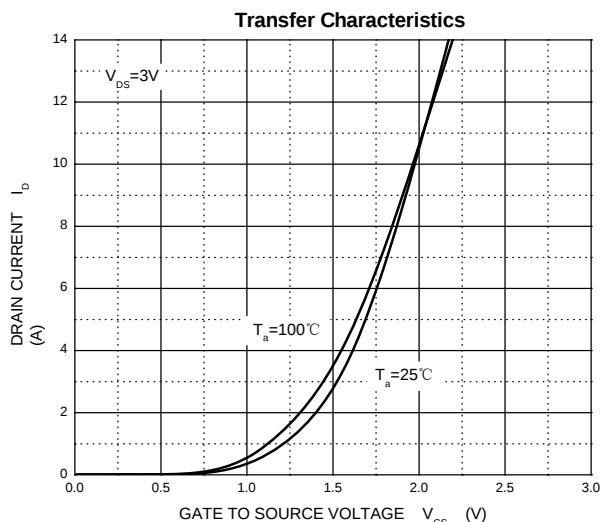
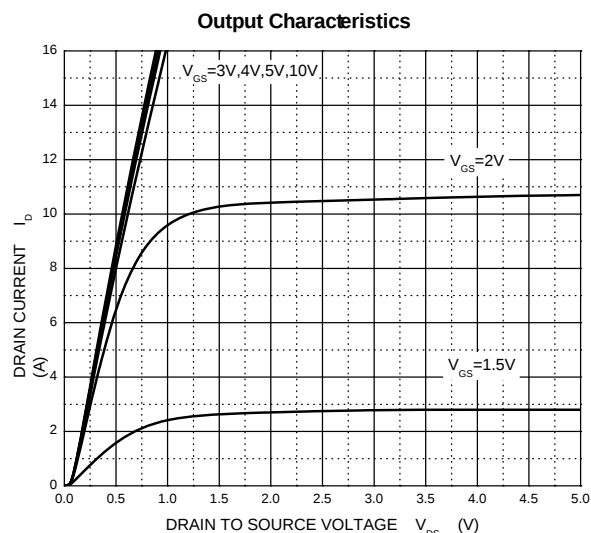
Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			100	nA
Gate threshold voltage (note 3)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.6		1.4	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4A$			45	m Ω
		$V_{GS} = 4.5V, I_D = 3A$			65	m Ω
		$V_{GS} = 2.5V, I_D = 2A$			100	m Ω
Forward transconductance (note 3)	g_{FS}	$V_{DS} = 15V, I_D = 4A$		8		S
Diode forward voltage (note 3)	V_{SD}	$I_S = 1A, V_{GS} = 0V$			1	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		390		pF
Output capacitance	C_{oss}			54.5		pF
Reverse transfer capacitance	C_{rss}			41		pF
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		3		Ω
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V,$ $R_L = 3.75\Omega, R_{GEN} = 6\Omega$		3.3		ns
Turn-on rise time	t_r			1		ns
Turn-off delay time	$t_{d(off)}$			21.7		ns
Turn-off fall time	t_f			2.1		ns
Total gate charge	Q_g	$V_{DS} = 15V, V_{GS} = 4.5V, I_D = 4A$		4.34		nC
Gate-source Charge	Q_{gs}			0.6		nC
Gate-drain Charge	Q_{gd}			1.38		nC
Body diode reverse recovery time	t_r	$I_F = 4A, dI/dt = 100A/\mu s$		1.2		ns
Body diode reverse recovery charge	Q_{rr}			6.3		nC

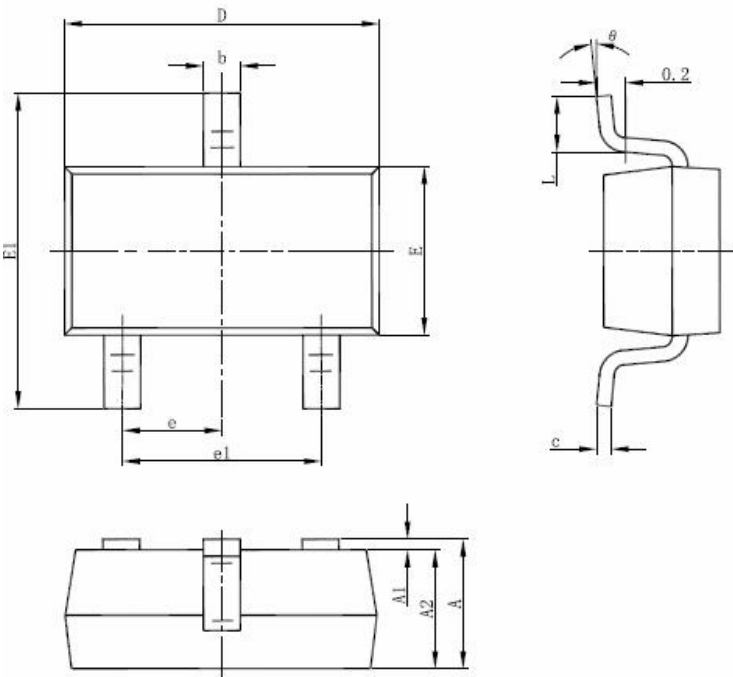
Notes :

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , $t \leq 10s$.
3. Pulse Test : Pulse Width $\leq 80\mu s$, Duty Cycle $\leq 0.5\%$.
4. Guaranteed by design, not subject to producing.

Typical Electrical and Thermal Characteristics



Package Mechanical Data-SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°